

APPLICATIONS

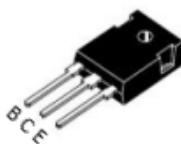
- Energy-saving light
- Electronic ballasts
- High frequency switching power supply
- High frequency power transform
- Commonly power amplifier

FEATURES

- High breakdown voltage
- High current capability
- High switching speed
- High reliability
- RoHS product

ABSOLUTE RATINGS (Tc=25°C)

Pulse Test: Pulse Width = 5.0 ms, Duty Cycle < 10%.



Parameter	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CBO}	700	V
Collector-Emitter Voltage	V _{CEO}	400	V
Emitter-Base Voltage	V _{EBO}	9	V
Collector Current (DC)	I _C	12	A
Base Current (DC)	I _B	12	A
Total Dissipation	P _{tot}	120	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55~+150	°C

DIM	MILLIMETERS	
	MIN	MAX
A	15	16
B	19.5	20.5
C	33.5	35.5
D	5	6
E	3.5	4.5
F	2.5	3.5
G	1.75	2.5
H	3	4
I	9	11
J	4.9	5.1
K	1	1.3
L	3.75	4.25
M	4.75	5.25
N	1.8	2.2
O	0.45	0.6
P	Typ 5.08	
Q	1.2	1.3

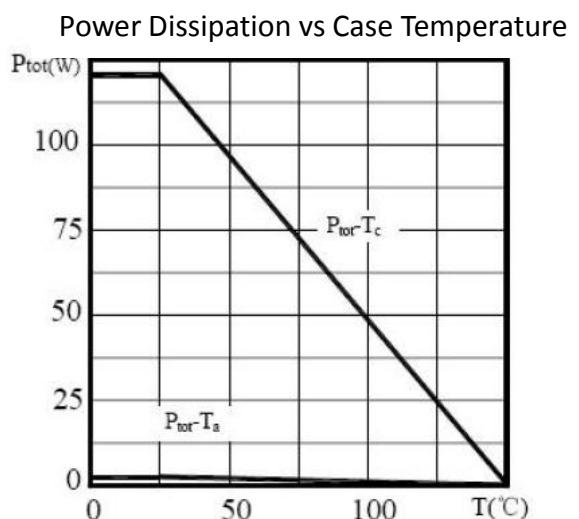
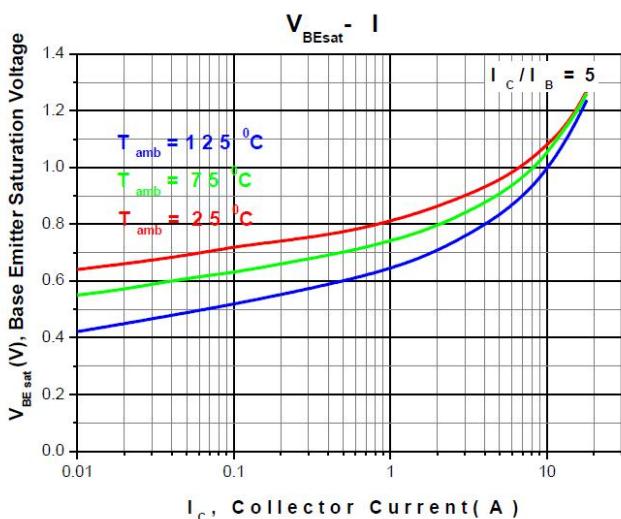
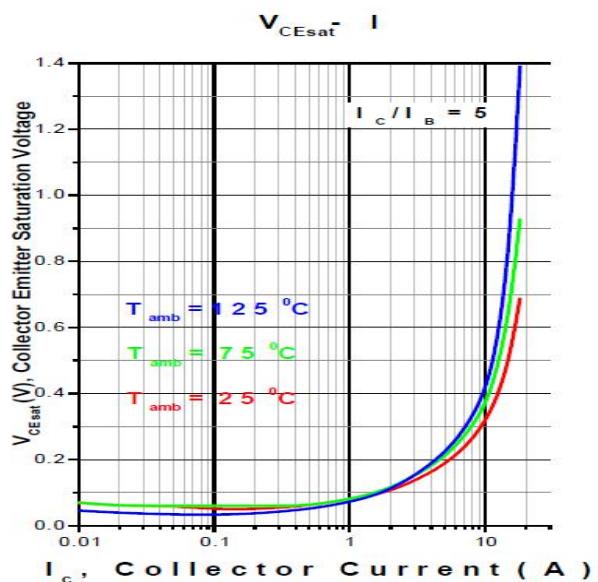
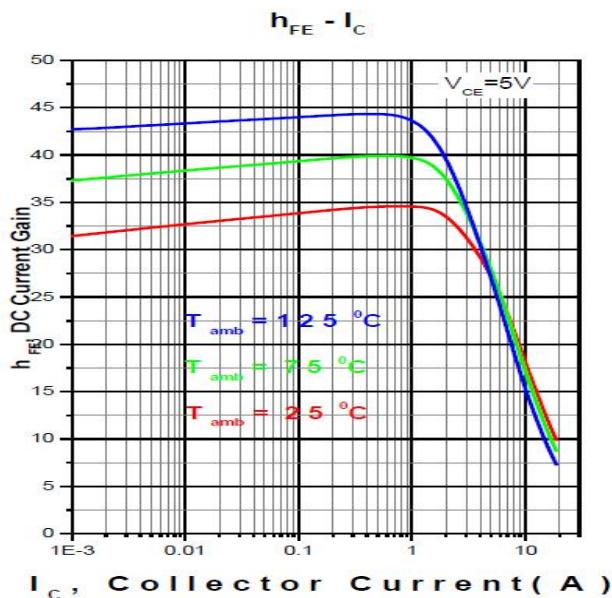
ELECTRICAL CHARACTERISTIC

Parameter	Tests conditions	Value(min)	Value(max)	Unit
V(BR)CEO	I _C =10mA, I _B =0	400	-	V
V(BR)CBO	I _C =1mA, I _B =0	700	-	V
V(BR)EBO	I _E =1mA, I _C =0	9	-	V
I _{CBO}	V _{CB} =700V, I _E =0	-	100	µ A
I _{CEO}	V _{CE} =400V, I _B =0	-	100	µ A
I _{EBO}	V _{EB} =9V, I _C =0	-	100	µ A
H _{fe}	V _{CE} =5V, I _C =5A	20	35	
V _{CE(sat)}	I _C =8A, I _B =1.6A	-	1.5	V
t _s	I _C =500mA	2	12	µ S
f _r	V _{CE} =10V, I _C =0.5A	4	-	MHz

Thermal Resistance

Symbol	Parameter	MAX.	Units	Test Conditions
R _{θJC}	Junction-to-Case	1.04	°C/W	Water cooled heatsink, P _D adjusted for a peak junction temperature of +150°C.

Characteristics Curve



Safe Operation Area(DC)

